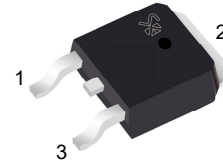


COMPLEMENTARY SILICON POWER TRANSISTORS

APPLICATIONS

SOLENOID/RELAY DRIVERS
GENERAL PURPOSE SWITCHING AND
AMPLIFIER



TO-252

1.Base 2. Collector 3.Emitter

TO-252 Plastic Package

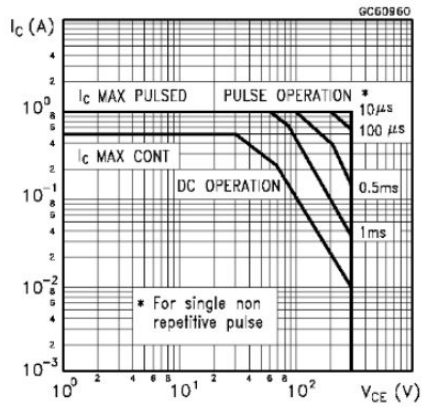
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	300	V
Collector Emitter Voltage	V_{CEO}	300	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	0.5	A
Collector Dissipation	P_C	625	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

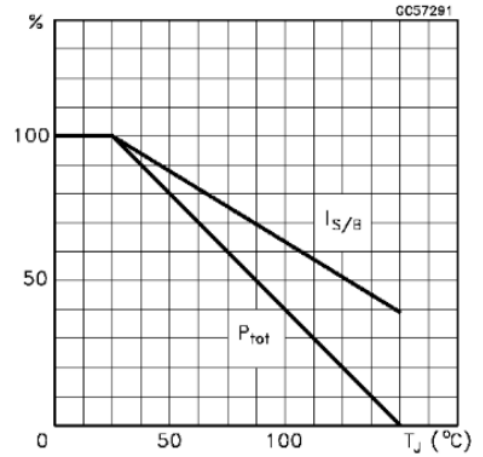
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Collector Base Cutoff Current at $V_{CB} = 35\text{ V}$	I_{CBO}	-	-	0.5	μA
Emitter Base Cutoff Current at $V_{EB} = 6\text{ V}$	I_{EBO}	-	-	0.5	μA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	300	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 2\text{ mA}$	$V_{(BR)CEO}$	300	-	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $I_C = 800\text{ mA}$, $I_B = 80\text{ mA}$	$V_{CE(sat)}$	-	-	0.5	V
Base Emitter Saturation Voltage at $I_C = 800\text{ mA}$, $I_B = 80\text{ mA}$	$V_{BE(sat)}$	-	-	1.0	V
DC Current Gain at $V_{CE} = 10\text{ V}$, $I_C = 10\text{ mA}$	h_{FE}	60		300	
Gain Bandwidth Product at $V_{CE} = 10\text{ V}$, $I_C = 50\text{ mA}$	f_T	50	-	-	MHz

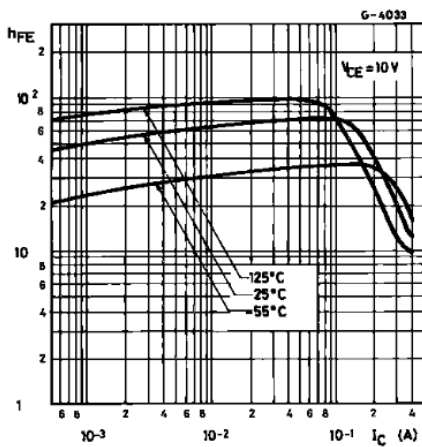
Safe Operating Area



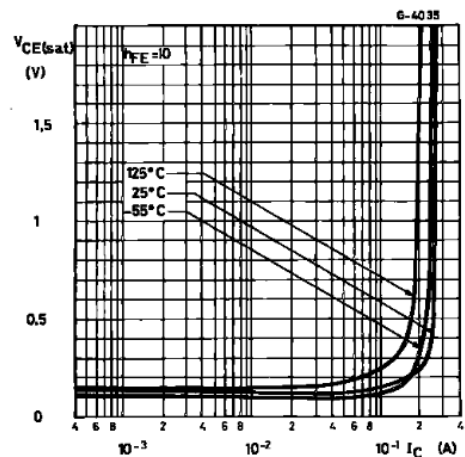
Derating Curve



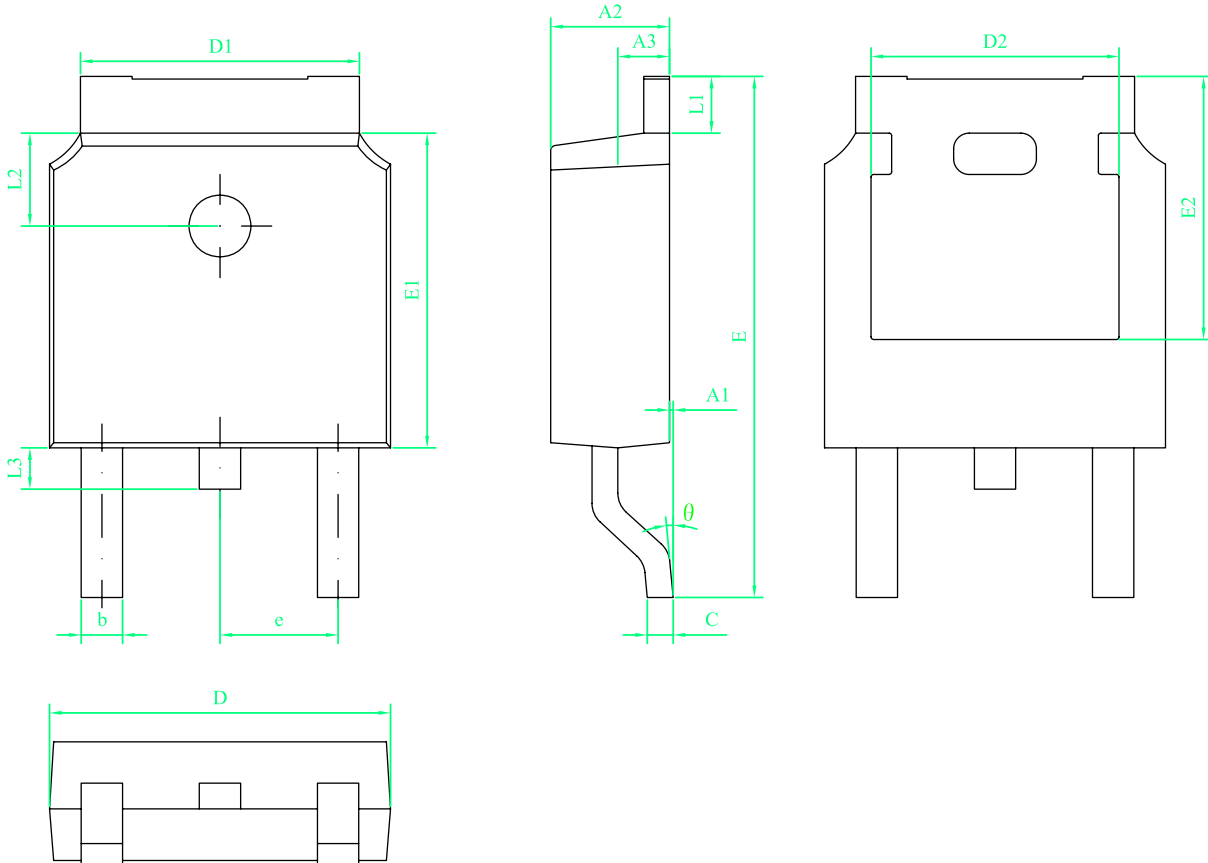
DC Current Gain



Collector Emitter Saturation Voltage



TO-252 PACKAGE OUTLINE



符号	尺寸	
	Min	Max
A1	0.00	0.13
A2	2.18	2.39
A3	0.90	1.10
b	0.65	0.85
c	0.46	0.61
D	6.35	6.73
D1	4.95	5.46
D2	4.32	
E	9.40	10.41
E1	5.97	6.22
E2	5.21	
e	2.286 BSC	
L1	0.89	1.27
L2	1.70	1.90
L3	0.60	1.00
θ	0.00	8.00

单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)